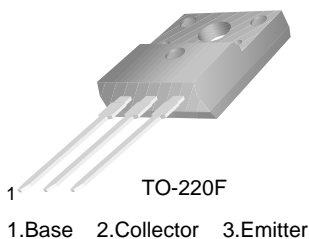


FJPF3305

High Voltage Switch Mode Application

- High Speed Switching
- Suitable for Electronic Ballast and Switching Regulator



Absolute Maximum Ratings * $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current (DC)	4	A
I_{CP}	Collector Current (Pulse)	8	A
I_B	Base Current	2	A
P_C	Collector Dissipation ($T_a = 25^\circ\text{C}$)	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-65 ~ 150	$^\circ\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics

* $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 500\mu\text{A}, I_E = 0$	700			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	400			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500\mu\text{A}, I_C = 0$	9			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 700\text{V}, I_E = 0$			1	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 9\text{V}, I_C = 0$			1	μA
h_{FE1} h_{FE2}	DC Current Gain *	$V_{CE} = 5\text{V}, I_C = 1\text{A}$ $V_{CE} = 5\text{V}, I_C = 2\text{A}$	19 8		35 40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1\text{A}, I_B = 0.2\text{A}$ $I_C = 2\text{A}, I_B = 0.5\text{A}$ $I_C = 4\text{A}, I_B = 1\text{A}$			0.5 0.6 1.0	V V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 1\text{A}, I_B = 0.2\text{A}$ $I_C = 2\text{A}, I_B = 0.5\text{A}$			1.2 1.6	V V
f_T	Current Gain Bandwidth Product	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	4			MHz
C_{ob}	Output Capacitance	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		65		pF
t_{ON}	Turn On Time	$V_{CC} = 125\text{V}$			0.8	μs
t_{STG}	Storage Time	$I_C = 2\text{A} = 5I_{B1} = -5I_{B2}$			4.0	μs
t_F	Fall Time	$R_L = 62.5\Omega$			0.9	μs

* Pulse Test: $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

h_{FE} Classification

Classification	H1	H2
h_{FE2}	19 ~ 28	26 ~ 35

Typical Performance Characteristics

Figure 1. Static Characteristic

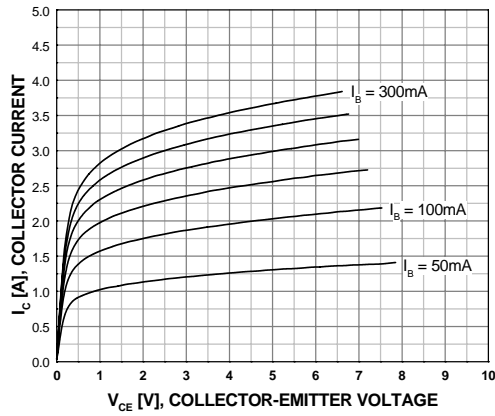


Figure 2. DC Current Gain (R-Grade)

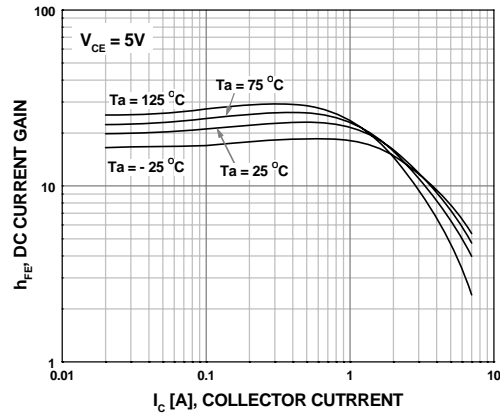


Figure 3. DC Current Gain (O-Grade)

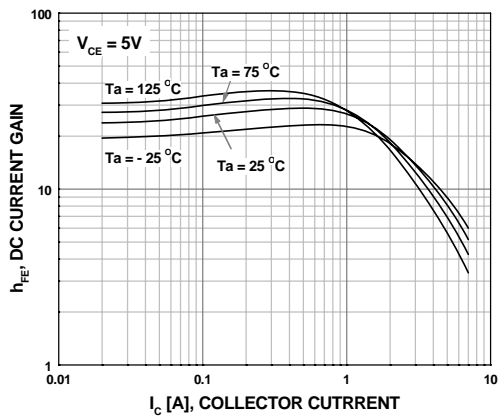


Figure 4. Saturation Voltage (R-Grade)

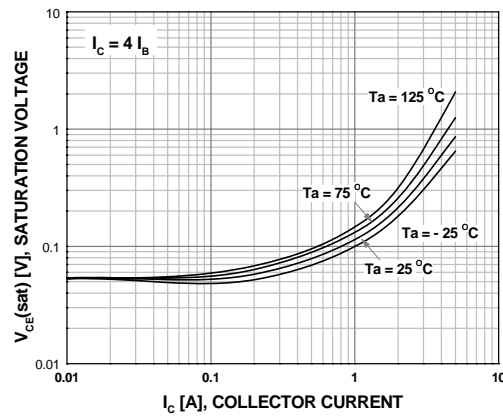


Figure 5. Saturatin Voltage (O-Grade)

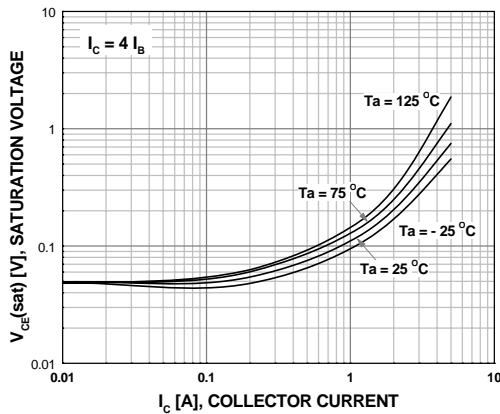
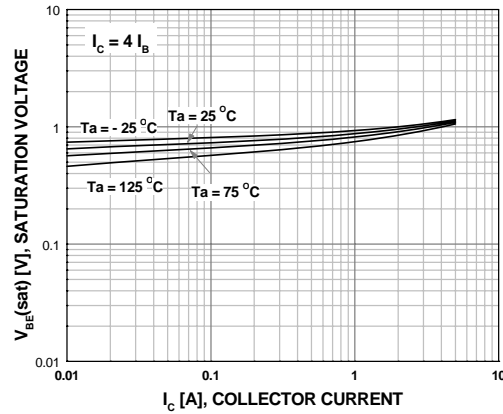


Figure 6. Saturation Voltage (R-Grade)



Typical Performance Characteristics (Continued)

Figure 7. Saturation Voltage (O-Grade)

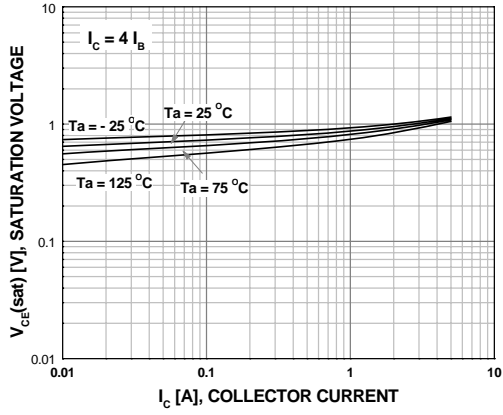


Figure 8. Switching Time

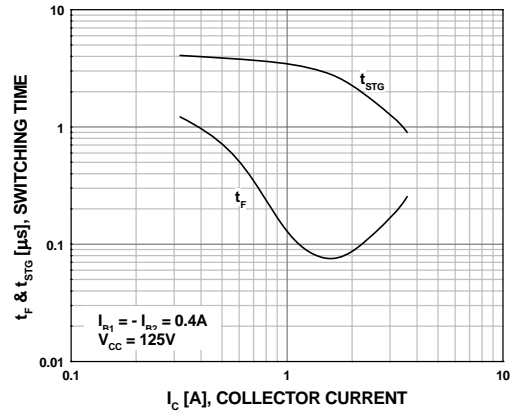


Figure 9. Reverse Biased Safe Operating Area

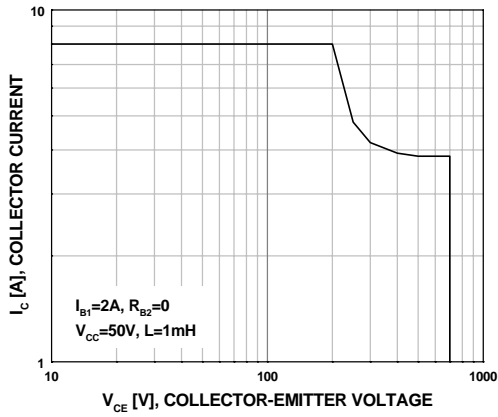


Figure 10. Forward Biased Safe Operating Area

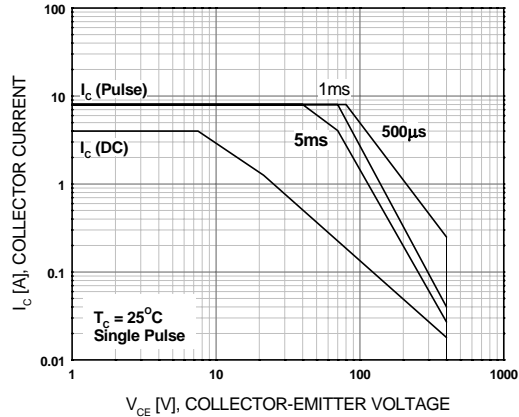
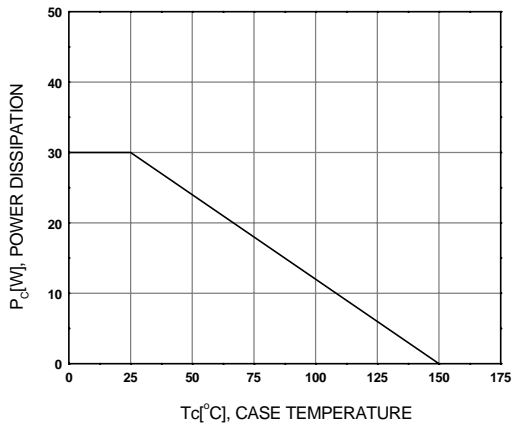
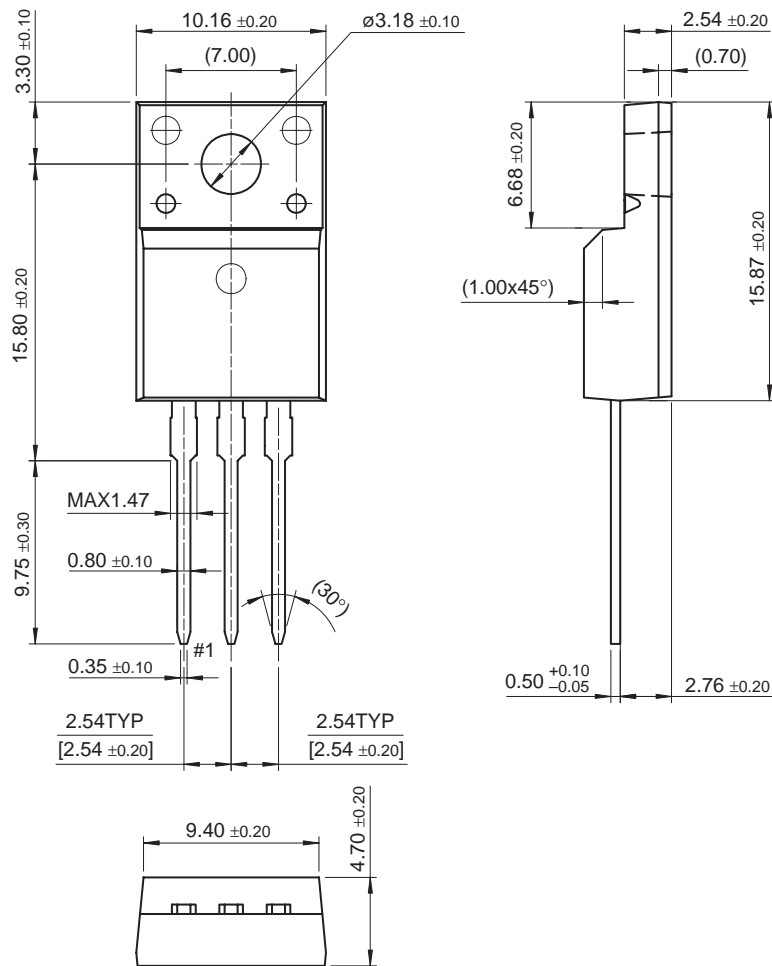


Figure 11. Power Derating



Mechanical Dimensions

TO-220F



Dimensions in Millimeters



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FACT®	OPTOPLANAR™®	SuperSOT™-6	
FAST®	PACMAN™	SuperSOT™-8	
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Rev. I23